

[제 27회 한국반도체학술대회] Program at a Glance

2월 12일(수)	5층		
	Room A	Room B	Room C
	컨벤션홀 L	에메랄드	사파이어
10:30~13:00	Short I-1		
13:00~14:00	점심 [그랜드볼룸 III / 4층] *Short Course 1 참가자에게만 제공		
14:00~18:00	Short I-2	Short II	Short III

2월 13일(목)	5층					6층							5-6층	5층
	Room A	Room B	Room C	Room D	Room E	Room F	Room G	Room H	Room I	Room J	Room K	Room L	로비	컨벤션홀 L
	에메랄드 I	에메랄드 II+III	사파이어 I	사파이어 II+III	루비 II	스페이드 I	스페이드 II+III	하트 I	하트 II	하트 III	다이아몬드 I	다이아몬드 II		
09:00~10:30	TA1-E Compound Semiconductor Technology I	TB1-F Emerging Device Technology I	TC1-R Semiconductor Software Optimization	TD1-G Modeling of Semiconductor Devies	TE1-L Analog	TF1-C 2D Materials	TG1-K Devices for Neuromorphic Computing I	TH1-N System & Circuit Design Analysis and Optimization	TI1-S Selected Papers on Chip Design Contest	TJ1-M RF Design I	TK1-D Thin Film Process I	TL1-J 페로브스카이트 LED - I	전시	ETRI 특별세션 (9:00~10:45)
10:30~10:45	휴식 (& 커피, 다과)													휴식 (10:45~11:00)
10:45~12:30	TA2-E Compound Semiconductor Technology II	TB2-F New Applications of Silicon Technology	TC2-H Image Engineering & Sensors	TD2-G Atomistic Modeling	TE2-SS Beyond 7-nm Technology	TF2-B Patterning Technology: Photolithography and Etch	TG2-K Emerging Memory I	TH2-J 뉴로모픽 소자 - I	TI2-A Interconnect & Packaging	TJ2-M RF Design II	TK2-D Thin Film Process II	TL2-J 소자 적용 나노 소재		KAERI 특별세션 (11:00~12:00)
12:30~14:00	점심 [그랜드볼룸 / 4층]													
14:00~14:50	기조강연 1 [컨벤션홀 K+W / 5층]													
14:50~15:00	휴식													
15:00~15:50	기조강연 2 [컨벤션홀 K+W / 5층]													
15:50~16:00	휴식 (& 커피, 다과)													
16:00~17:45	포스터 세션 1 [5층 로비 및 컨벤션홀 L]													
17:45~18:00	휴식													
18:00~20:00	만찬													
20:00~22:00	Rump Session I [에메랄드홀 / 5층]		Rump Session II [사파이어홀 / 5층]											

2월 14일(금)	5층					6층							5-6층
	Room A	Room B	Room C	Room D	Room E	Room F	Room G	Room H	Room I	Room J	Room K	Room L	로비
	에메랄드 I	에메랄드 II+III	사파이어 I	사파이어 II+III	루비 II	스페이드 I	스페이드 II+III	하트 I	하트 II	하트 III	다이아몬드 I	다이아몬드 II	
09:00~10:30	FA1-E Compound Semiconductor Technology III	FB1-F Emerging Device Technology II	FC1-H OLED & Display Technology	FD1-G Characterization of Semiconductor Devices	FE1-I Gas Sensing Technology	FF1-C Wide Bandgap Materials I (Ga2O3 & etc)	FG1-K Emerging Memory II	FH1-Q Nanoanalysis and Characterization	FI1-P Low Dimensional Materials: Peorpties and Energy Device Applications	FJ1-D 2-dimensional System I	FK1-D Ferroelectric Materials	FL1-J 페로브스카이트 양자점	전시
10:30~10:45	휴식 (& 커피, 다과)												
10:45~12:30	FA2-O Artificial Intelligent Circuits and Systems	FB2-F Neuromorphic Technology	FC2-H Oxide Thin-Film Transistors	FD2-G TCAD Simulation and Beyond	FE2-I Chemical and Biological Sensors	FF2-C Wide Bandgap Materials II (SiC, diamond & etc)	FG2-K Devices for Neuromorphic Computing II	FH2-Q Metrology, Inspection, and Yield Enhancement	FI2-P Next Generation Battery Devices	FJ2-D 2-dimensional System II	FK2-D Thin Film Process III	FL2-J 페로브스카이트 LED - II	
12:30~14:00	점심 [그랜드볼룸 / 4층]												
14:00~15:30	포스터 세션 2 [5층 로비 및 컨벤션홀 L]												
15:30~15:45	휴식												
15:45~17:30	FA3-O VLSI System Design and Application	FB3-F Nano-electromechanical and 3D Integration Technology	FC3-H TFTs & Display Technology	FD3-G Compact Modeling	FE3-I MEMS and Sensor Systems for Biomedical Applications	FF3-C Wide Bandgap Materials I (Oxide & Nitride)	FG3-K Emerging Memory III	FH3-J 양자점 & 뉴로모픽 소자 - II	FI3-P Photo-Catalytic Mateirias for Energy Devices	FJ3-D Memory Devices	FK3-D Thin Film Transistors	FL3-J 이차원 물질	
17:30~17:45	폐회식												